

BC860

Rev.F Apr.-2017

VRW056

SQS

Silicon PNP transistor in a SOT-23 Plastic Package.

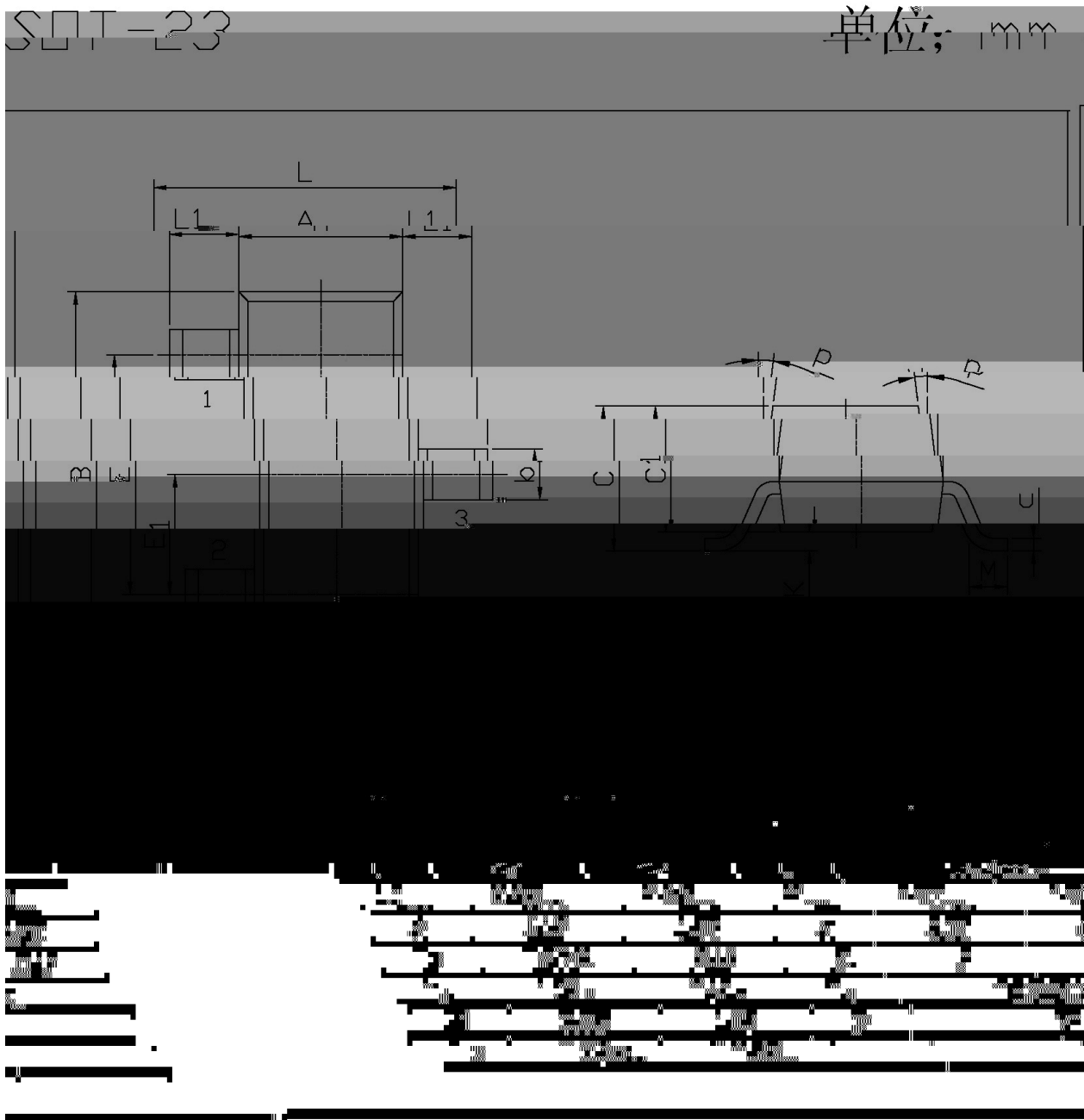
$V_{CE(sat)}$

High current gain, Low collector-emitter saturation voltage.

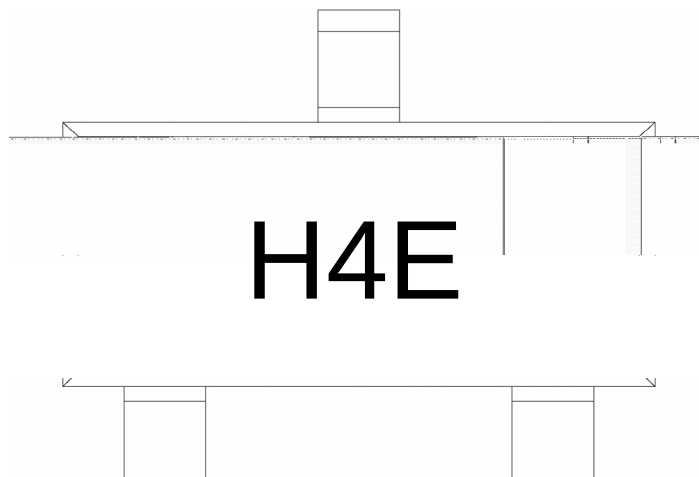
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-50	V
Collector to Emitter Voltage	V_{CEO}	-45	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	I_C	-100	mA
Collector Power Dissipation	P_C	350	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C = -10mA$ $I_B = 0$	-45			V
Collector to Base Breakdown Voltage	V_{CBO}	I_C I_E				

/ Package Dimensions



/ Marking Instructions



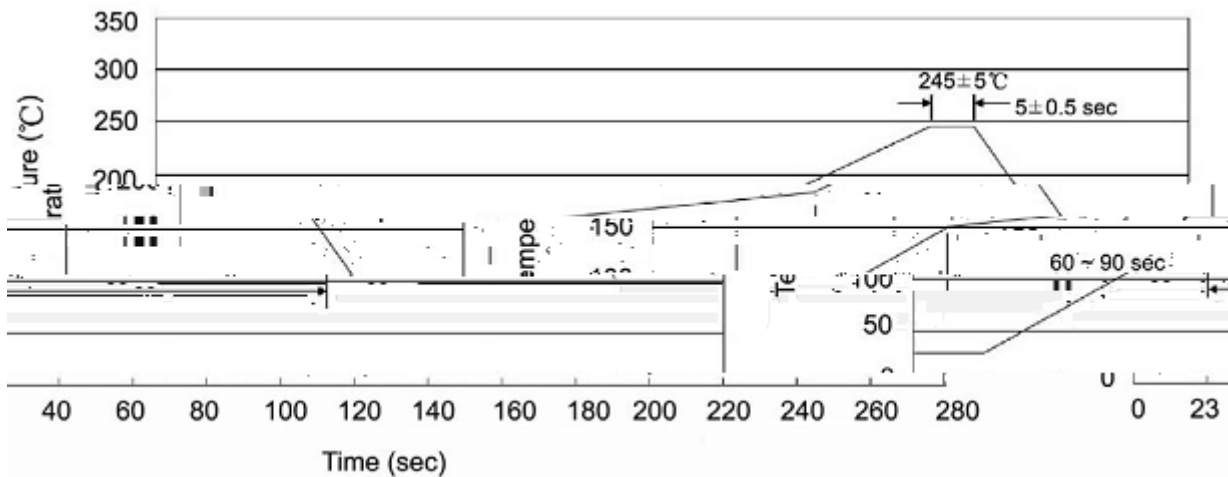
K

7H

Note:

H: Company Code.

4E: Product Type Code


() / Temperature Profile for IR Reflow Soldering(Pb-Free)


Note:

- | | | | | | |
|---|-----|------|----------|----------|---|
| 1 | 25 | 150% | 60 | 90sec; | 1.Preheating:25~150%, Time:60~90sec. |
| 2 | 245 | ±5% | 5 | ±0.5sec; | 2.Peak Temp.:245 ± 5%, Duration:5 ± 0.5sec. |
| 3 | | 2 | 10%/sec. | | 3. Cooling Speed: 2~10%/sec. |

/ Resistance to Soldering Heat Test Conditions

260±5

10±1 sec.

Temp.:260±5

Time:10±1 sec

/ Packaging SPEC.

/ REEL

Package Type	Units					Dimension (unit mm ³)		
	Units/Reel	Reels/Inner Box	Units/Inner Box	Inner Boxes/Outer Box	Units/Outer Box	Reel	Inner Box	Outer Box
SOT-23	3,000	10	30,000	6	180,000	7 ×8	180×120×180	390×385×205

/ Notices